

2N3663



NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	12	V
V _{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	3.0	V
Ic	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

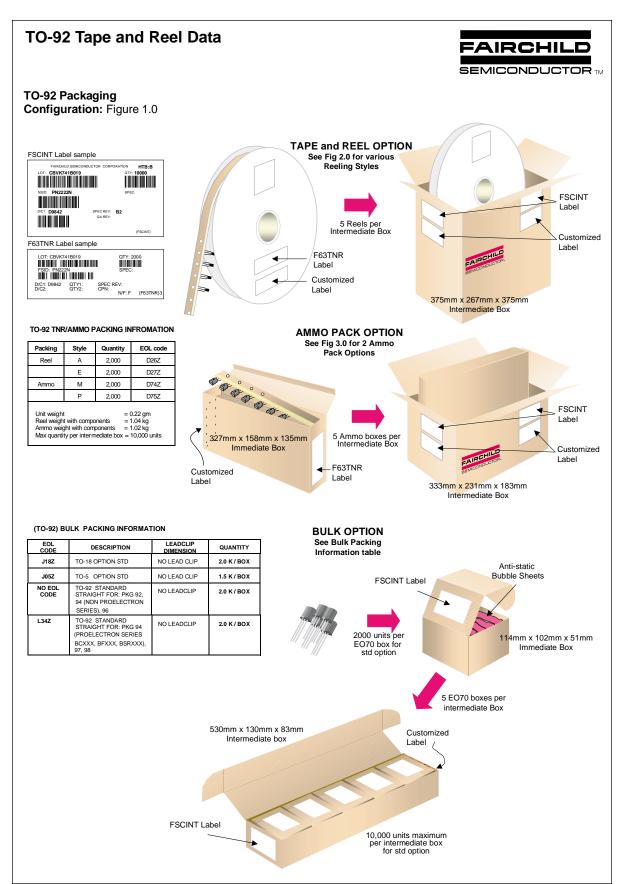
Symbol	Characteristic	Max	Units
		2N3663	
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

NPN RF Transistor

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
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	RACTERISTICS		1	1	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	12		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	3.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$		0.5	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_{C} = 0$		0.5	μΑ
	RACTERISTICS* DC Current Gain	$V_{CE} = 10 \text{ V}, I_{C} = 8.0 \text{ mA}$	20		
h _{FE}		$V_{CE} = 10 \text{ V}, I_{C} = 8.0 \text{ mA}$	20		
h _{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_{C} = 8.0 \text{ mA}$ $I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	700	2100	MHz
h _{FE}	DC Current Gain	$I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$		2100	MHz
SMALL S	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	700		
SMALL SI f _T C _{ob} rb'C _C	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\begin{split} I_{C} &= 5.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz} \\ I_{C} &= 8.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \end{split}$	700	1.7	pF
SMALL SI f _T C _{ob} rb'C _C	DC Current Gain GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant	$\begin{split} I_{C} &= 5.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz} \\ I_{C} &= 8.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \end{split}$	700	1.7	pF

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

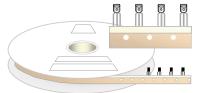


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

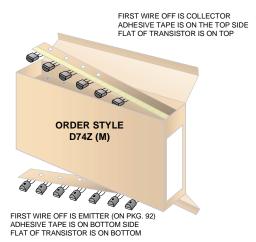


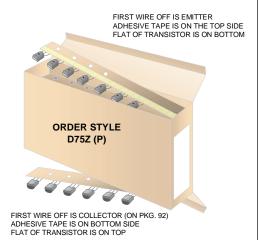
Style "A", D26Z, D70Z (s/h)

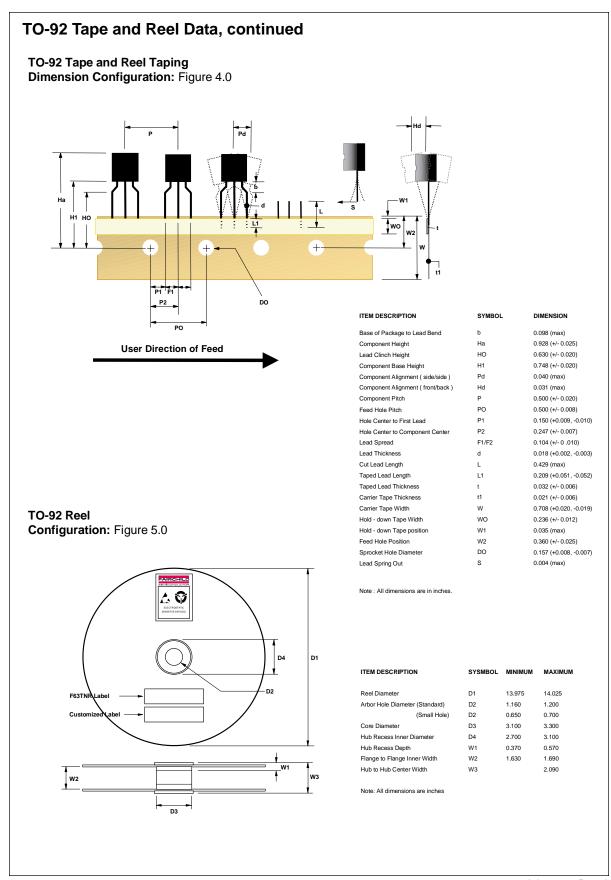
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





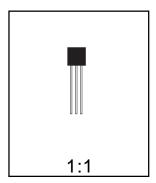


TO-92 Package Dimensions



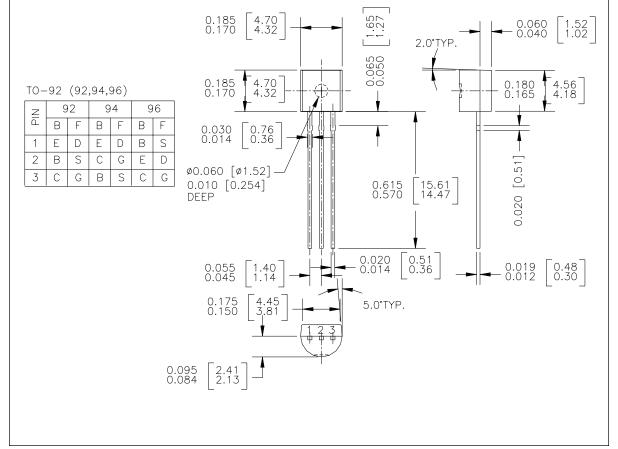
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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